SamHop Microelectronics Corp.

STU/D421S

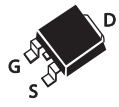
Aug.20,2006

P-Channel Logic Level Enhancement Mode Field Effect Transistor

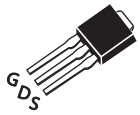
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
-40V	-10A	45 @ V_{GS} = -10V
		60 @ V_{GS} = -4.5V

FEATURES

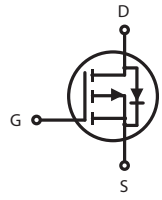
- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- TO-252 and TO-251 Package.



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous [a] @Ta	25°C	I_D	-10	A
	70°C		-8.3	A
-Pulsed [b]		I_{DM}	-50	A
Drain-Source Diode Forward Current [a]		I_S	-10	A
Maximum Power Dissipation [a]	Ta= 25°C	P_D	50	W
	Ta=70°C		35	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	°C/W

STU/D421S

P-Channel ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [c]	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250uA	-40			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-32V, V_{GS}= 0V			1	uA
Gate-Body Leakage	I_{GSS}	V_{GS}=±20V, V_{DS}= 0V			±100	nA
ON CHARACTERISTICS [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250uA	-1.0	-1.7	-3.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D= -10A		34	45	m ohm
		V_{GS}=-4.5V, I_D= -6A		47	60	m ohm
On-State Drain Current	$I_{D(ON)}$	V_{DS}=-5V, V_{GS} = -10V	30			A
Forward Transconductance	g_{FS}	V_{DS} = -10V, I_D = -10A		11		S
DYNAMIC CHARACTERISTICS [c]						
Input Capacitance	C_{ISS}	V_{DS} =-20V, V_{GS} = 0V f =1.0MHz		900		pF
Output Capacitance	C_{OSS}			135		pF
Reverse Transfer Capacitance	C_{RSS}			85		pF
Gate resistance	Rg	V_{GS} =0V, V_{DS} = 0V, f=1.0MHz		3.5		ohm
SWITCHING CHARACTERISTICS [c]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD} = -24V I_D = -10 A V_{GS} = -10V R_{GEN} = 3.3 ohm		12		ns
Rise Time	t_r			15		ns
Turn-Off Delay Time	$t_{D(OFF)}$			45		ns
Fall Time	t_f			26		ns
Total Gate Charge	Q_g	VDS =-24V, ID =-10A,VGS =-10V		17		nC
		VDS =-24V, ID =-10A,VGS =-4.5V		8		nC
Gate-Source Charge	Q_{gs}	V_{DS} =-24V, I_D = -16A V_{GS} =-10V		1.8		nC
Gate-Drain Charge	Q_{gd}			5		nC

STU/D421S

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS [a]						
Diode Forward Voltage	V_{SD}	V_{GS} = 0V, Is = -10A		-0.91	-1.3	V

Notes

a.Pulse Test:Pulse Width ≤300us, Duty Cycle ≤2%.

b.Guaranteed by design, not subject to production testing.

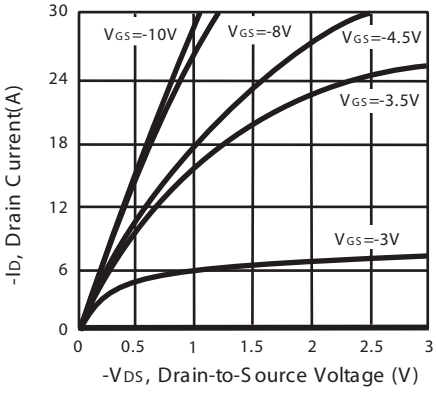


Figure 1. Output Characteristics

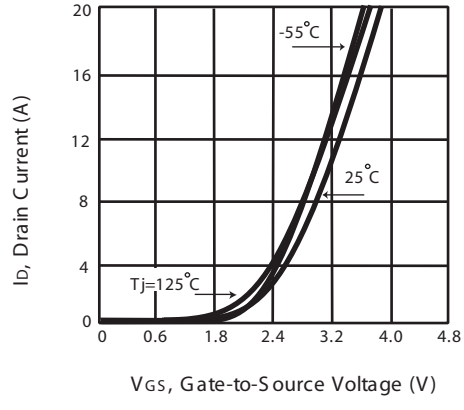


Figure 2. Transfer Characteristics

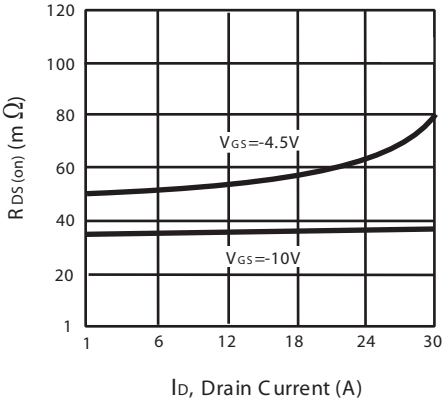


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

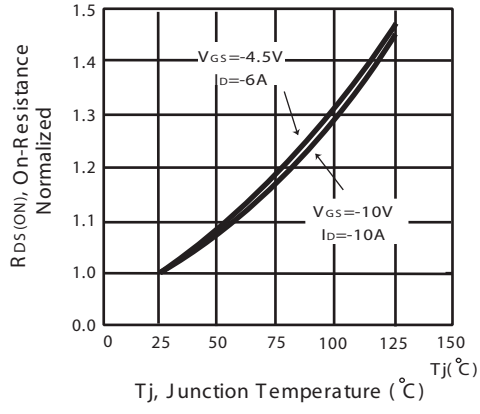


Figure 4. On-Resistance Variation with Drain Current and Temperature

STU/D421S

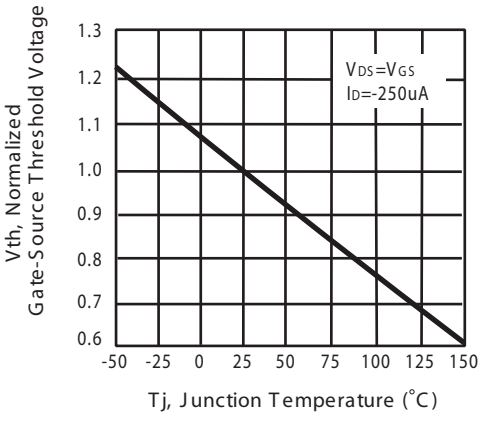


Figure 5. Gate Threshold Variation with Temperature

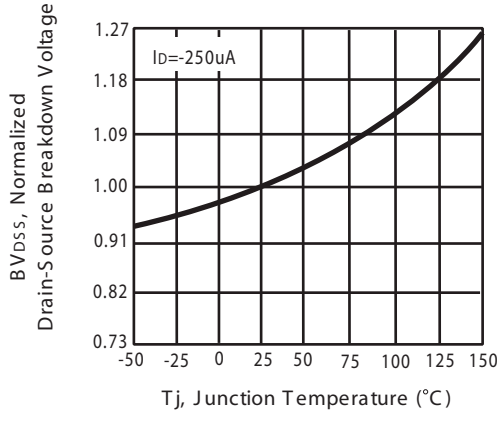


Figure 6. Breakdown Voltage Variation with Temperature

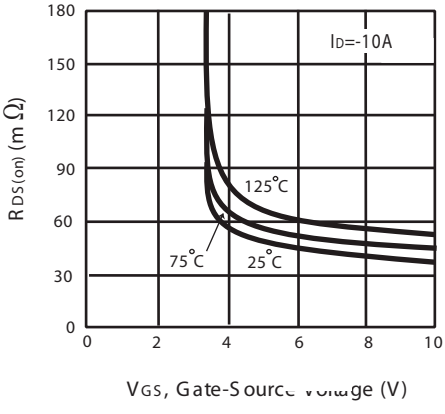


Figure 7. On-Resistance vs. Gate-Source Voltage

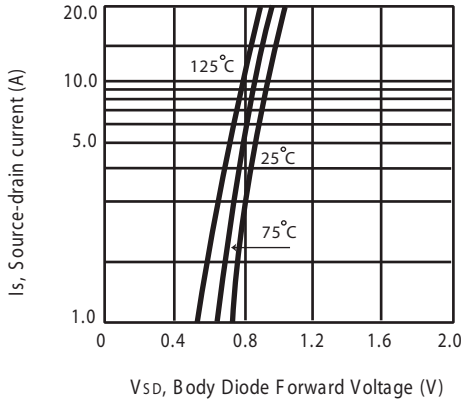


Figure 8. Body Diode Forward Voltage Variation with Source Current

STU/D421S

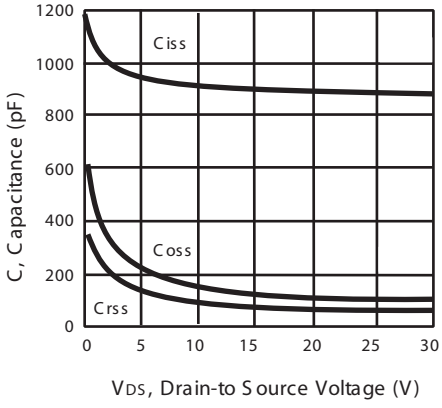


Figure 9. Capacitance

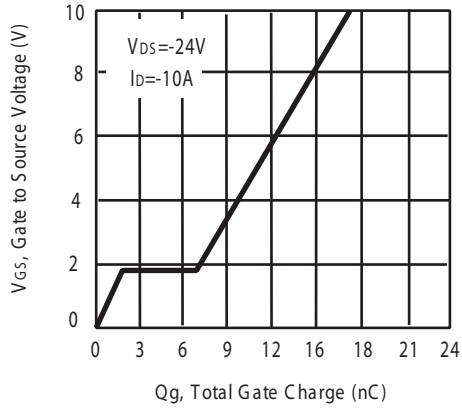


Figure 10. Gate Charge

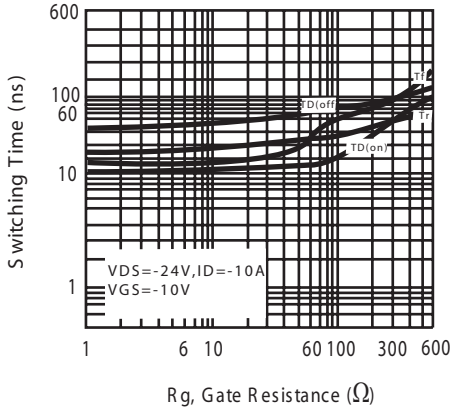


Figure 11.switching characteristics

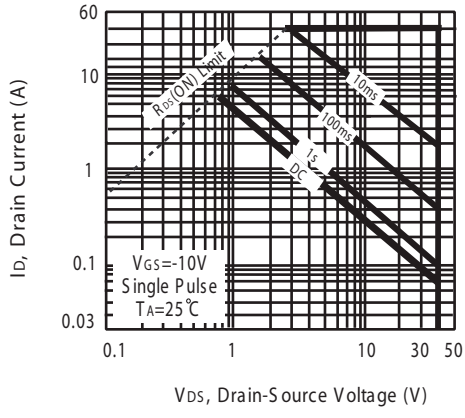


Figure 12. Maximum Safe Operating Area

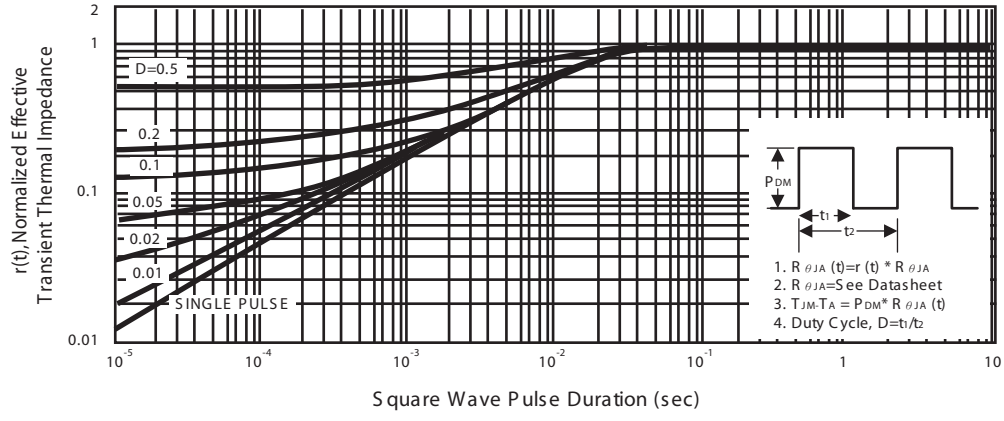
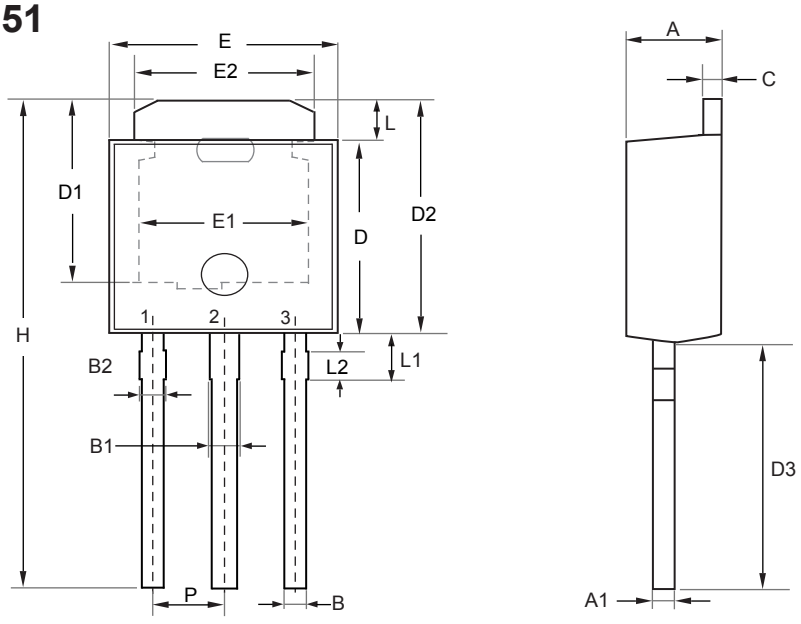


Figure 13. Normalized Thermal Transient Impedance Curve

STU/D421S

PACKAGE OUTLINE DIMENSIONS

TO-251

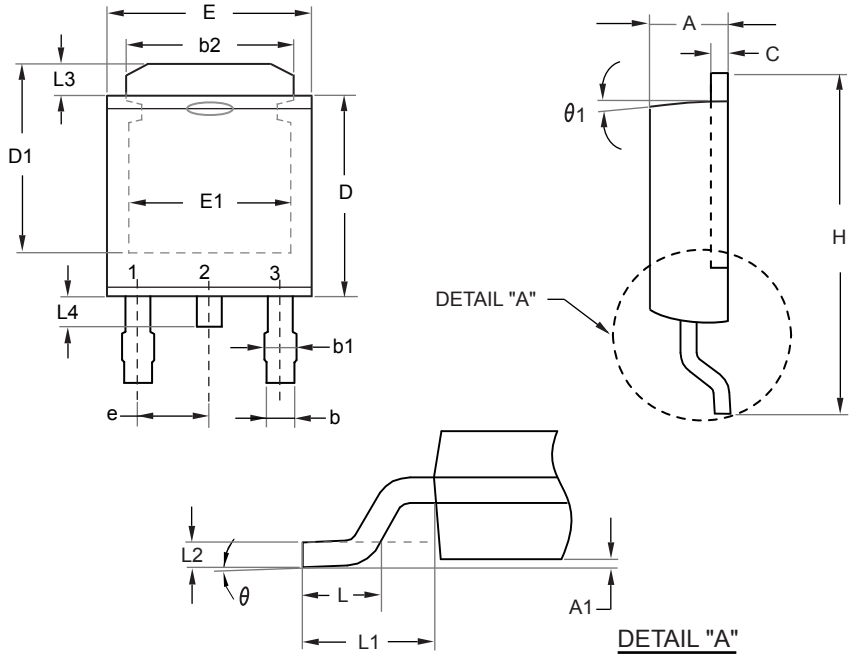


SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.350	0.650	0.014	0.026
B	0.400	0.800	0.016	0.031
B1	0.650	1.050	0.026	0.041
B2	0.500	0.900	0.020	0.035
C	0.400	0.600	0.016	0.024
D	5.300	5.700	0.209	0.224
D1	4.900	5.300	0.193	0.209
D2	6.700	7.300	0.264	0.287
D3	7.000	8.000	0.276	0.315
H	13.700	15.300	0.539	0.602
E	6.300	6.700	0.248	0.264
E1	4.600	4.900	0.181	0.193
E2	4.800	5.200	0.189	0.205
L	1.300	1.700	0.051	0.067
L1	1.400	1.800	0.055	0.071
L2	0.500	0.900	0.020	0.035
P	2.300 BSC		0.091 BSC	

STU/D421S

PACKAGE OUTLINE DIMENSIONS

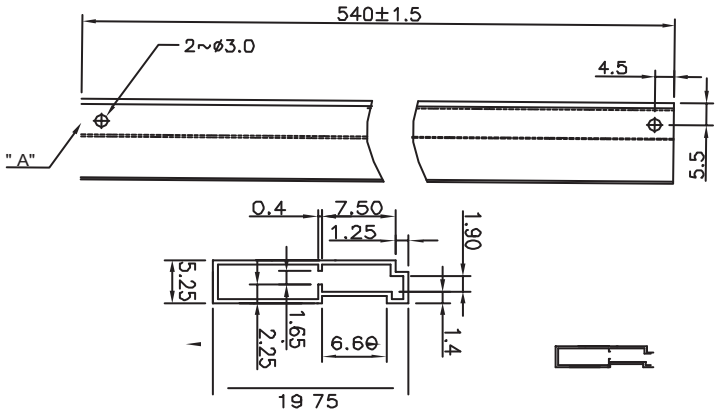
TO-252



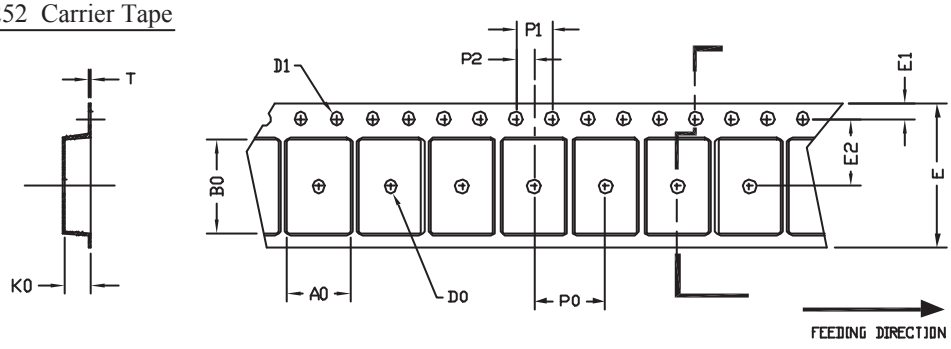
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.400	5.004	0.173	0.197
e	2.290 REF		0.090 BSC	
H	8.900	10.400	0.350	0.409
L	1.397	1.770	0.055	0.070
L1	2.743 REF.		0.108 REF.	
L2	0.508 REF.		0.020 REF.	
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
θ	0°	10°	0°	10°
θ1	7° REF.		7° REF.	

TO251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



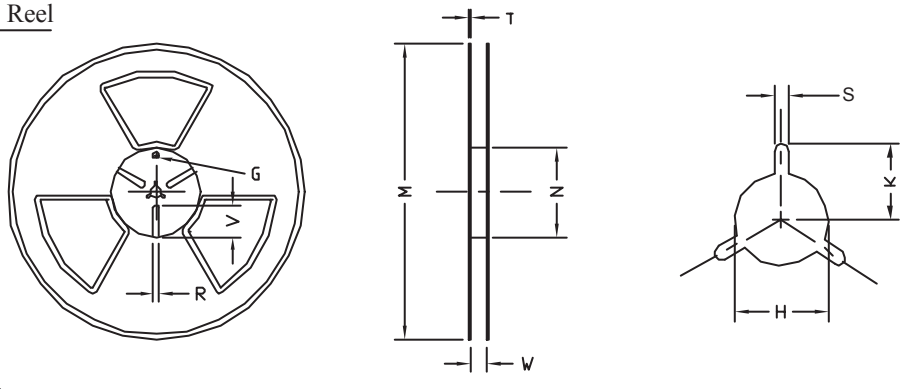
TO-252 Carrier Tape



UNIT:㎜

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 ㎜)	6.80 ±0.1	10.3 ±0.1	2.50 ±0.1	ϕ2	ϕ1.5 +0.1 -0	16.0 0.3±	1.75 0.1±	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:㎜

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 ㎜	ϕ 330	ϕ330 ± 0.5	ϕ97 ± 1.0	17.0 +1.5 -0	2.2	ϕ13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---